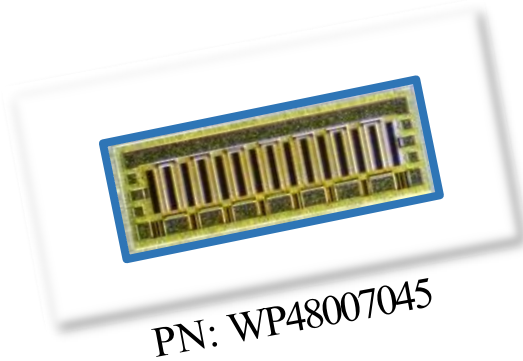




WP48007045

45W, 48V GaN HEMT Die



The WP48007045 is a 45W gallium nitride (GaN) High Electron Mobility Transistor (HEMT). This GaN HEMT is a wideband transistor optimized for 5.8GHz operation in a user-friendly device for high bandwidth applications. Gallium nitride (GaN) HEMT is a device optimized for 5G. GaN HEMT resistance is only 1/10 that of silicon transistors, making it capable of switching frequencies faster for greater energy efficiency.

Features

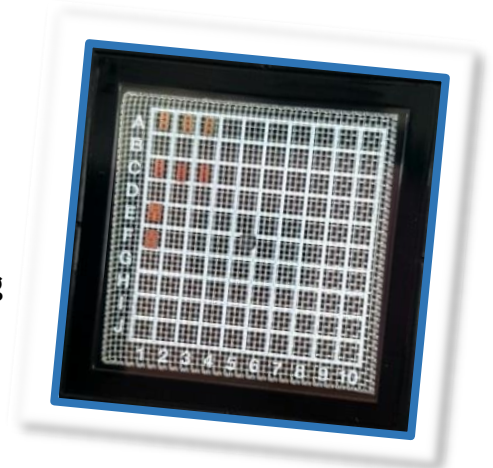
- Up to 8 GHz Operation
- 14.0 dB Typical Small Signal Gain @ 3.5 GHz
- 45 W Typical Psat @5.8GHz
- 48V Operation
- High Breakdown Voltage
- High Breakdown Voltage
- High Efficiency
- Reliability Monitoring Supporting

Applications

- U/VHF Amplifiers
- Broadband Amplifiers
- Base Station Communications
- Drone, UAV
- WiMAX, LTE, WCDMA, GSM
- WPT, V2X
- Radar application

Packaging Information

- Bare die are shipped in Wafer-level with Expander Ring or Gel-Pak® containers.
- Possible UV Curing for Wafer-level with dicing saw



Absolute Maximum Ratings (not simultaneous) at 25 °C

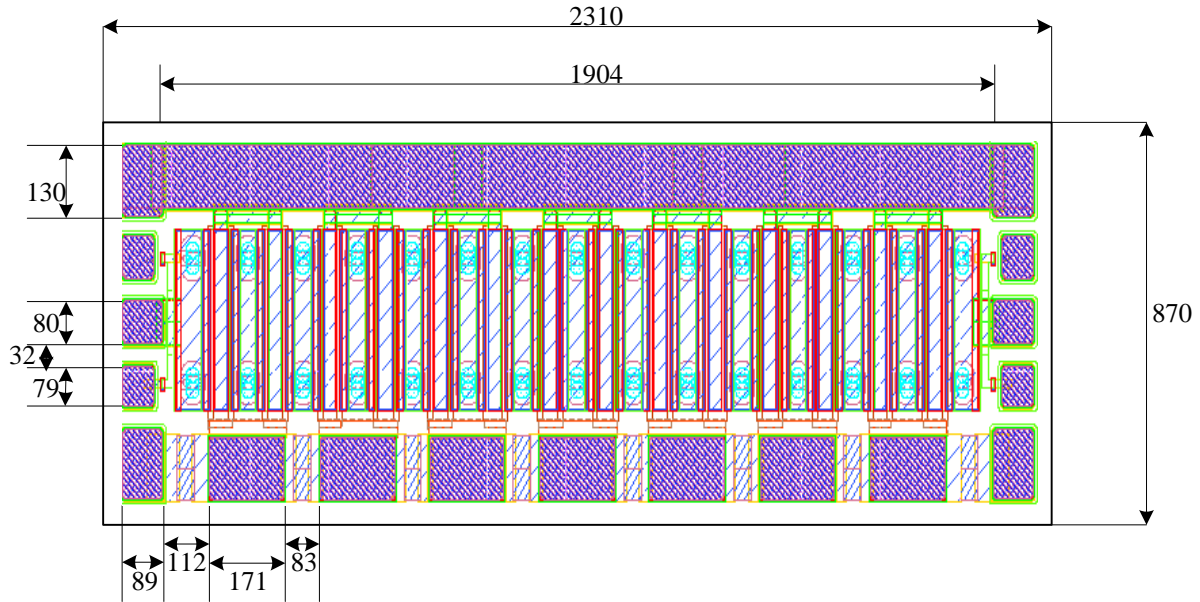
Parameter	Parameter	Typical Value	Units	Conditions
Threshold voltage @ Id=1mA/mm, Vd=10V	V _{to}	-3.4	V	25°C
Breakdown voltage @ Id=1mA/mm	V _{DG}	160	V	25°C
Drain-source current, Id @ Vd=10V, Vg=0	I _{dss}	800	mA/mm	25°C
Operating Junction Temperature	T _J	225	°C	
Storage Temperature	T _{STG}	-65, +150	°C	
Thermal Resistance, Junction to Case (packaged)	R _{θJC}		°C/W	
Thermal Resistance, Junction to Case (die only)	R _{θJC}		°C/W	
Mounting Temperature (30 seconds)	T _S	320	°C	30 seconds

Electrical Characteristics (Frequency = 3.5 GHz unless otherwise stated; TC = 25 °C)

Parameter	Parameter	Typical Value	Units	Conditions
DC Characteristics				
Ohmic contact resistance	RC	0.3	Ohm-mm	25°C
Maximum Drain-source current, Id @ Vd=10V, Vg=1V (1X125µm device)	I _{dmax}	1000	mA/mm	25°C
Max. trans-conductance, @ Vd=10V, Vg=-4V ~ -1V (1X125µm device)	GM_PEAK	290	mS/mm	25°C
Maximum Drain-source current, Id @ Vd=10V, Vg=1V (1X125µm device)	I _{dmax}	1000	mA/mm	25°C
RF Characteristics				
Small Signal Gain	G _{SS}	>12	dB	V _{DD} =48V, I _{DQ} =300mA
Saturated Power Output	P _{SAT}	45	W	V _{DD} =48V, I _{DQ} =300mA
Drain Efficiency	η	>60	%	V _{DD} =48V, I _{DQ} =300mA
Intermodulation Distortion	IM3	<-30	dBc	V _{DD} =48V, I _{DQ} =300mA
Output Mismatch Stress	VSWR	10:1	ψ	



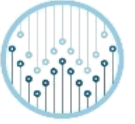
DIE Dimensions (units in microns)



Overall die size 2310 x 870 (+0/-50) microns, die thickness 100 (+/- 10) microns.
All Gate and Drain pads must be wire bonded for electrical connection.

Assembly Notes:

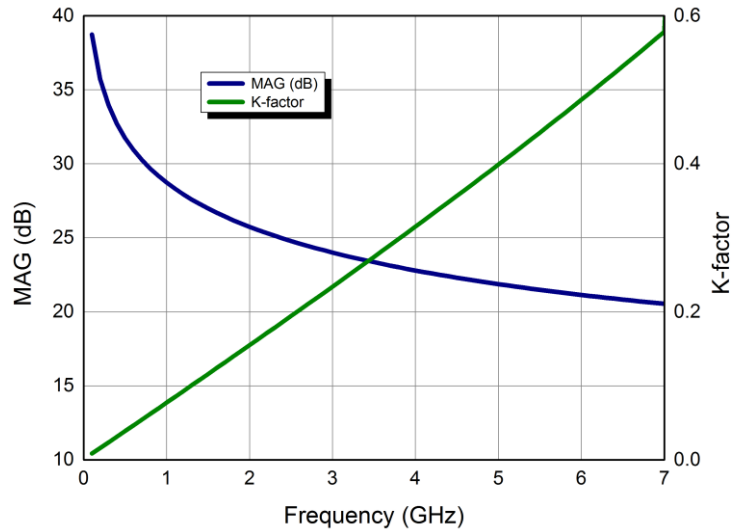
- Recommended solder is AuSn (80/20) solder. Refer to Wavepia’s guide for the Eutectic Die Bond Procedure
- Vacuum collet is the preferred method of pick-up.
- The backside of the die is the Source (ground) contact.
- Die back side gold plating is 5 microns thick minimum.
- Thermosonic ball or wedge bonding are the preferred connection methods.
- Gold wire must be used for connections.



Typical Performance

Simulated Maximum Available Gain (MAG) and K Factor of the WP48007045

$$V_{DD} = 48 \text{ V}, I_{DQ} = 300 \text{ mA}$$

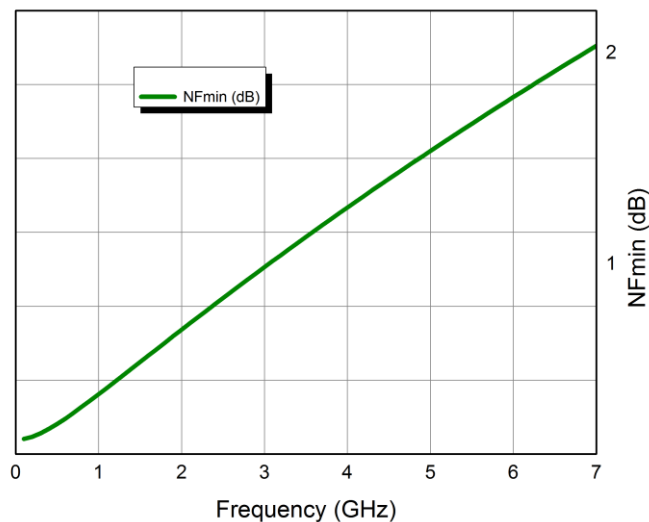


Intrinsic die parameters - reference planes at centers of gate and drain bonding pads. No wire bonds assumed.

Typical Performance

Simulated Minimum Noise Figure of the WP48007045

$$V_{DD} = 48 \text{ V}, I_{DQ} = 300 \text{ mA}$$





Typical Die S-Parameters

(Small Signal, $V_{DS} = 48\text{ V}$, $I_{DQ} = 300\text{ mA}$, magnitude / angle)

Frequency	Mag S11	Ang S11	Mag S21	Ang S21	Mag S12	Ang S12	Mag S22	Ang S22
100MHz	0.972215	-77.9488	61.42908	138.6989	0.00823	48.81337	0.34077	-122.695
200MHz	0.950458	-116.485	41.03242	118.1598	0.010994	28.3887	0.454357	-143.933
300MHz	0.941997	-135.064	29.56317	107.7066	0.01188	18.05	0.492626	-153.043
400MHz	0.938417	-145.444	22.82918	101.3077	0.012231	11.76563	0.509931	-157.603
500MHz	0.936743	-151.958	18.49993	96.8047	0.012388	7.377102	0.520167	-160.089
600MHz	0.935945	-156.392	15.50631	93.32024	0.012459	4.007143	0.527666	-161.487
700MHz	0.935612	-159.591	13.31957	90.44278	0.012484	1.244191	0.534065	-162.261
800MHz	0.935558	-162.001	11.65412	87.9564	0.012481	-1.12766	0.540068	-162.651
900MHz	0.935686	-163.877	10.34374	85.73785	0.01246	-3.23167	0.546007	-162.799
1000MHz	0.935945	-165.376	9.285652	83.712	0.012425	-5.14297	0.552043	-162.79
1100MHz	0.936302	-166.6	8.413056	81.83066	0.01238	-6.90974	0.558251	-162.68
1200MHz	0.936738	-167.617	7.680761	80.06163	0.012327	-8.56418	0.564664	-162.506
1300MHz	0.937237	-168.474	7.057133	78.38263	0.012266	-10.1286	0.571286	-162.295
1400MHz	0.93779	-169.206	6.519385	76.77784	0.012199	-11.6187	0.57811	-162.065
1500MHz	0.938388	-169.839	6.050698	75.23572	0.012126	-13.0462	0.585119	-161.828
1600MHz	0.939026	-170.39	5.638395	73.74772	0.012049	-14.4195	0.592289	-161.594
1700MHz	0.939697	-170.876	5.272737	72.30734	0.011967	-15.7452	0.599597	-161.37
1800MHz	0.940398	-171.306	4.946125	70.9096	0.011881	-17.0282	0.607018	-161.161
1900MHz	0.941123	-171.691	4.652543	69.5506	0.011791	-18.2724	0.614525	-160.969
2000MHz	0.94187	-172.038	4.387163	68.22724	0.011698	-19.4809	0.622094	-160.796
2100MHz	0.942635	-172.351	4.14607	66.93704	0.011603	-20.6563	0.6297	-160.644
2200MHz	0.943414	-172.637	3.926051	65.67796	0.011504	-21.8005	0.637322	-160.514
2300MHz	0.944205	-172.898	3.724448	64.44834	0.011403	-22.9152	0.644938	-160.405
2400MHz	0.945005	-173.139	3.539039	63.24675	0.0113	-24.0018	0.65253	-160.317
2500MHz	0.945811	-173.362	3.367954	62.072	0.011195	-25.0615	0.660079	-160.25
2600MHz	0.946622	-173.568	3.209609	60.92305	0.011089	-26.0954	0.66757	-160.202
2700MHz	0.947435	-173.761	3.062647	59.79898	0.010981	-27.1044	0.674988	-160.173
2800MHz	0.948248	-173.942	2.925904	58.69898	0.010872	-28.0893	0.682322	-160.163
2900MHz	0.94906	-174.112	2.798374	57.62231	0.010762	-29.0507	0.689559	-160.169
3000MHz	0.949869	-174.272	2.679181	56.56831	0.010651	-29.9895	0.69669	-160.191
3100MHz	0.950673	-174.424	2.567559	55.53636	0.01054	-30.9061	0.703707	-160.228
3200MHz	0.951471	-174.569	2.462837	54.52586	0.010428	-31.8013	0.710603	-160.278
3300MHz	0.952262	-174.706	2.364421	53.53627	0.010316	-32.6754	0.717371	-160.342
3400MHz	0.953045	-174.837	2.271785	52.56707	0.010204	-33.5291	0.724008	-160.416
3500MHz	0.953818	-174.963	2.184462	51.61775	0.010092	-34.3629	0.730509	-160.502
3600MHz	0.954582	-175.083	2.102033	50.68782	0.00998	-35.1772	0.736871	-160.597
3700MHz	0.955335	-175.199	2.024125	49.77683	0.009868	-35.9725	0.743093	-160.701
3800MHz	0.956076	-175.311	1.950401	48.88431	0.009757	-36.7493	0.749172	-160.813
3900MHz	0.956806	-175.419	1.880557	48.00982	0.009646	-37.5079	0.755107	-160.933

Contact WAVEPIA to receive this s-parameter file in “.s2p” format at platune@wavepia.com



Disclaimer

Information furnished by WAVEPIA Co., Ltd. is believed to be accurate and reliable. However, no responsibility is assumed by WAVEPIA Co., Ltd. for its use, nor for any infringements of patents or other rights of third parties that may result from its use. The information contained is provided "as it is" and with all defects, and the whole risk associated with such information is entirely with the user. Specifications subject to change without notice. WAVEPIA Co., Ltd. and registered trademarks are the property of their respective owners. Customers must search and verify the updated information before placing orders for our products. We makes no guarantee or representation regarding the information contained herein the using of products for any specific purpose. WAVEPIA Co., Ltd. products are not warranted or authorized for use as key components in conditions, or other applications where a failure would be expected to cause severe personal injury or death.

For more information, please contact :

- *For more details : WAVEPIA Co., Ltd.*
- *#1301, 557, Dongtangiheung-ro, Hwaseong-si, Gyeonggi-do, Republic of Korea*
- *Application Support: platune@wavepia.com*

Sanghun Lee
CTO
WAVEPIA, IC DESIGN
+82.31.8058.3374